

# Quality Test of the KLOE-IT GEM foils

*Danilo Domenici  
on behalf of the KLOE-IT group*

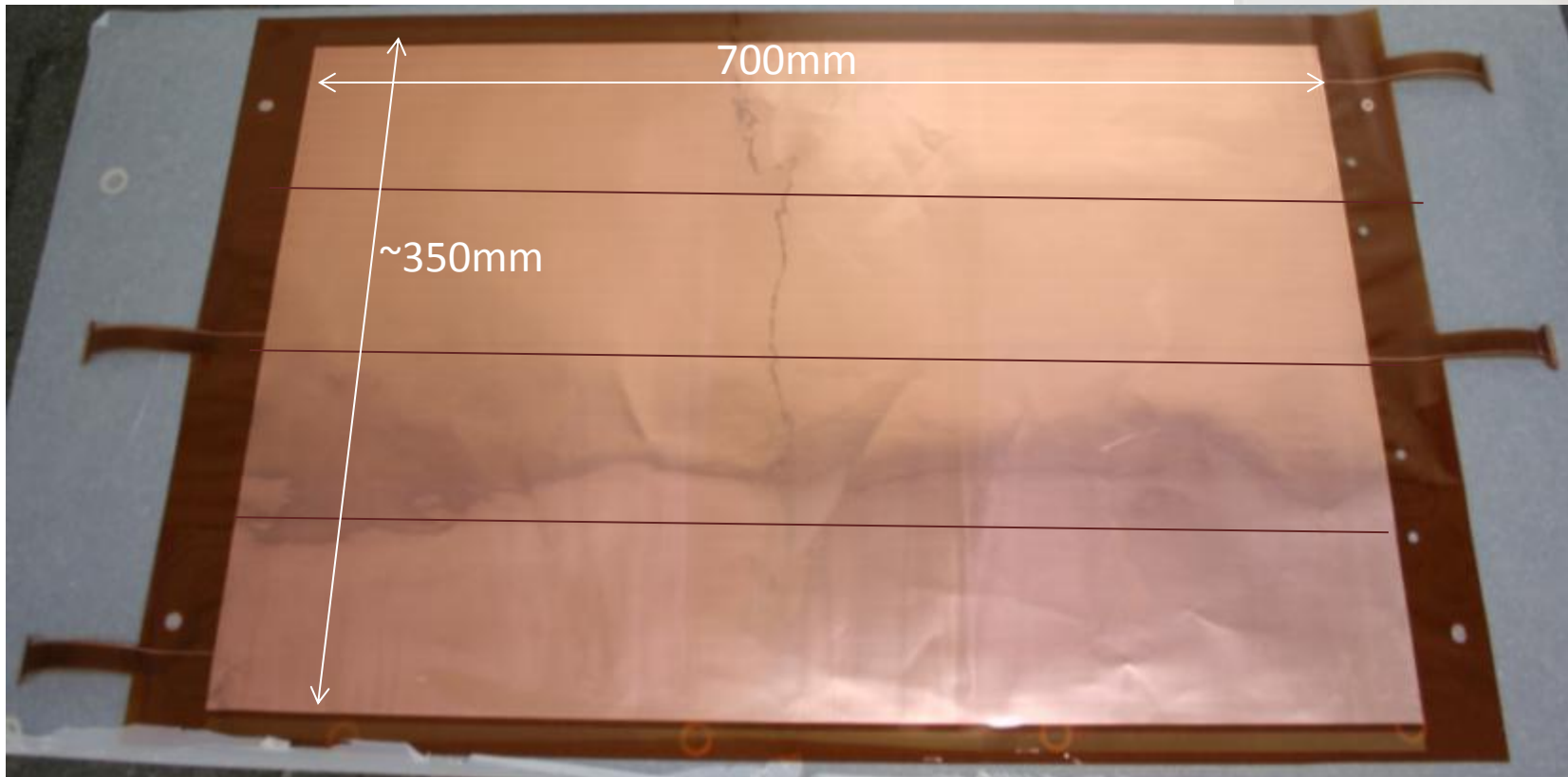
# The KLOE IT GEM foil

N.4 macro-sectors on the bottom side

N.40 micro-sectors (80 cm<sup>2</sup>) on the top side

All the HV connections are brought to the bottom side through vias, filled with conductive silver glue.

Detail of the HV connection with the 10+1 vias

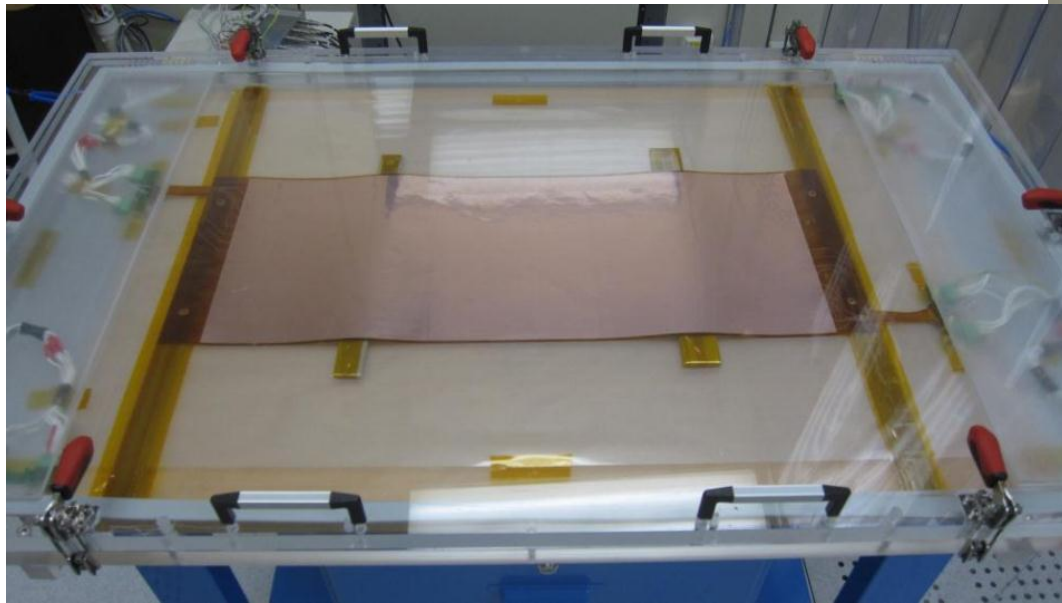
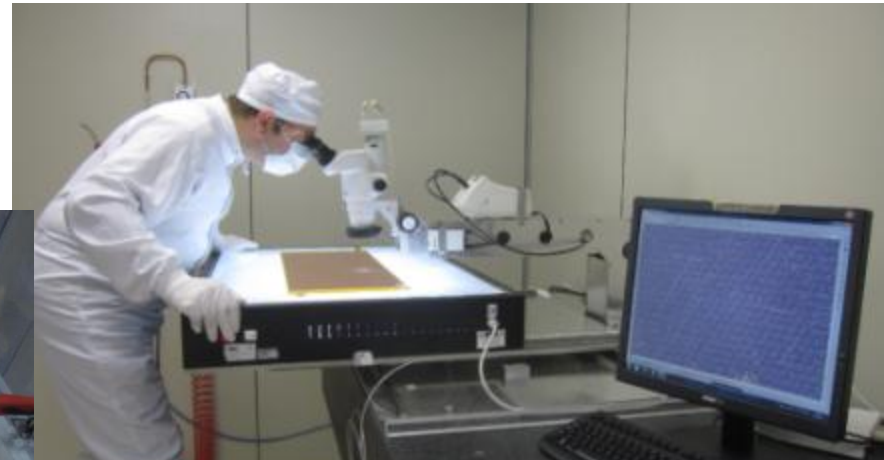


# HV test & Visual Inspection

The quality of GEMs is checked with HV in a N<sub>2</sub> flushed box, for humidity reduction (<10% RH).

During the test each sector of the GEM foil is supplied up to 600 V. Discharge rate and leakage current are monitored.

HV connections are also checked to have  $R < 2 \text{ Ohm}$



A complete test of a GEM foil takes > 4 hours

# Details of GEM test

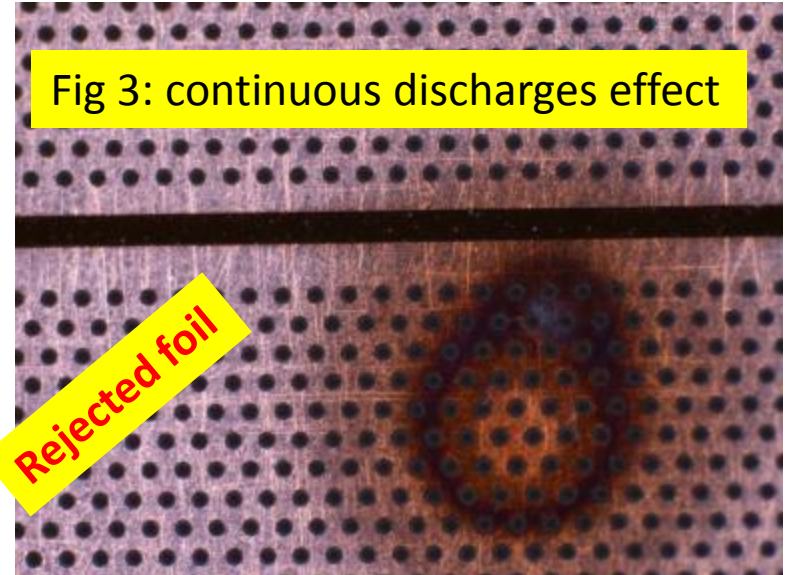
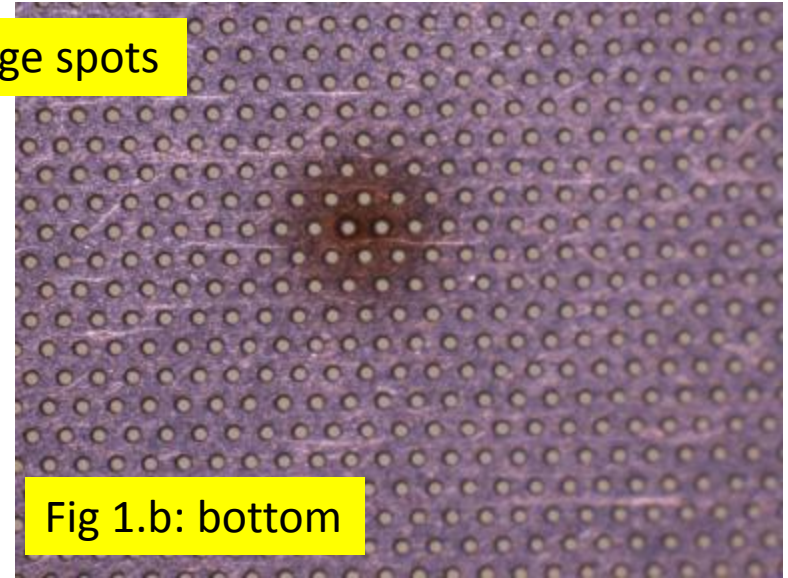
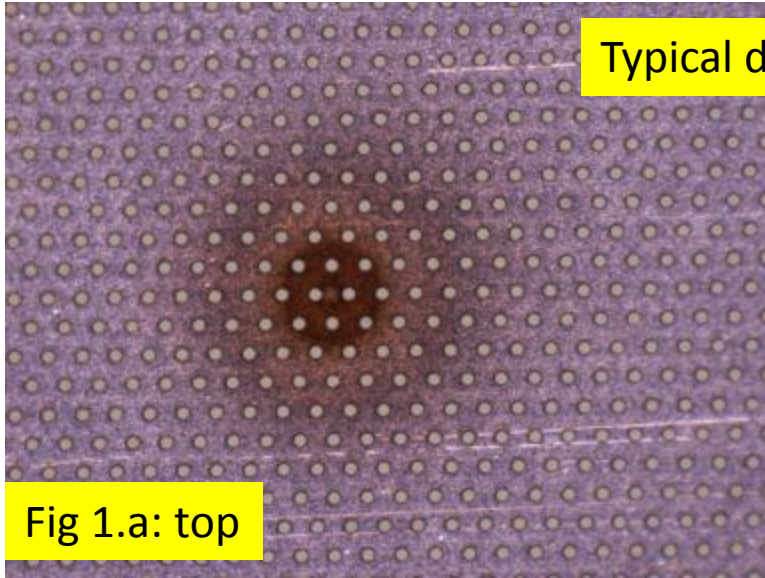
LAYER 1				LAYER 3			
Problems	Actions	Outcome	Comments	Problems	Actions	Outcome	Comments
L1G1A		OK	fig. 1a,b	L3G1A	over-etching	BAD	
L1G1B		OK		L3G1B		OK	
L1G1C		OK	fig. 2	L3G1C		OK	fig. 6
L1G1D	5 nA @ 600 V	none	BAD	L3G1D		OK	
L1G2A		OK		L3G2A		OK	
L1G2B	short-circuit on 1 sector	none	BAD	L3G2B	continous discharges	back to CERN	
L1G2C		OK			HV tail resistance > 2 Ohm	BAD	
L1G2D		OK		L3G2C	5 nA @ 600 V; short-circuit on S18;	back to CERN	OK
L1G3A		OK		L3G2D		OK	
L1G3B		OK		L3G3A		OK	
L1G3C	150 nA @ 450 V and discharge spots	none	BAD	fig. 3	L3G3B	1000 nA @ 600 V	none
L1G3D		OK			L3G3C		OK
					L3G3D		OK
LAYER 2				LAYER 4			
L2G1A		OK		L4G1A		OK	
L2G1B		OK		L4G1B	3 over-etching; 1 short-circuit	none	BAD
L2G1C	cut by blade on two HV tracks	none	BAD	L4G1C		OK	fig. 7a,b,c
L2G1D		OK	fig. 4a,b	L4G1D		OK	
L2G1E	continous discharge (over-etching)	none	BAD	fig. 5a,b	L4G2A	bad etching quality between microsectors	back to CERN
L2G1F		OK			L4G2B		OK
L2G2A		OK		L4G2C		OK	
L2G2B	300 nA @ 590 V	back to CERN	OK	L4G2D	150 nA @ 600 V	back to CERN	OK
L2G2C	6 nA @ 600 V; over-etching; HR-HV tail;	back to CERN					
	HV tail resistance > 2 Ohm	back to CERN	BAD	L4G3A		OK	
L2G2D		OK		L4G3B		OK	
L2G3A		OK		L4G3C		OK	
L2G3B	80 nA @ 450V;	back to CERN		L4G3D		OK	
	HV tail resistance > 2 Ohm		BAD				
L2G3C	120 nA @ 450 V	back to CERN	OK				
L2G3D	HR-HV tail	back to CERN	OK				

# Summary

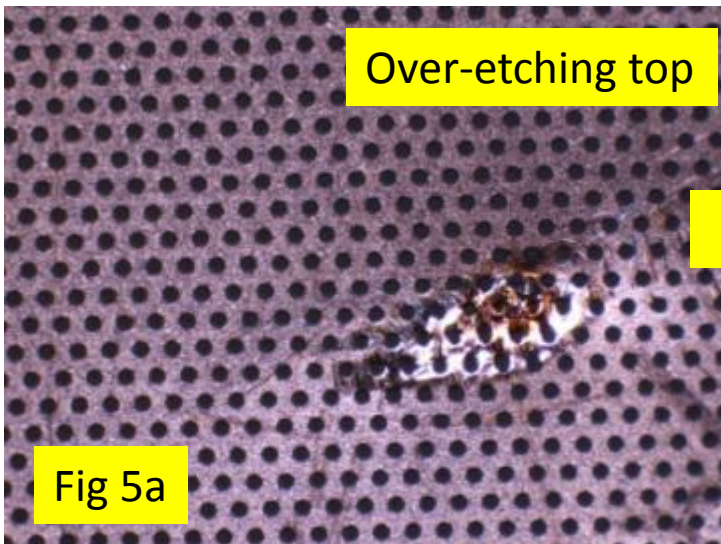
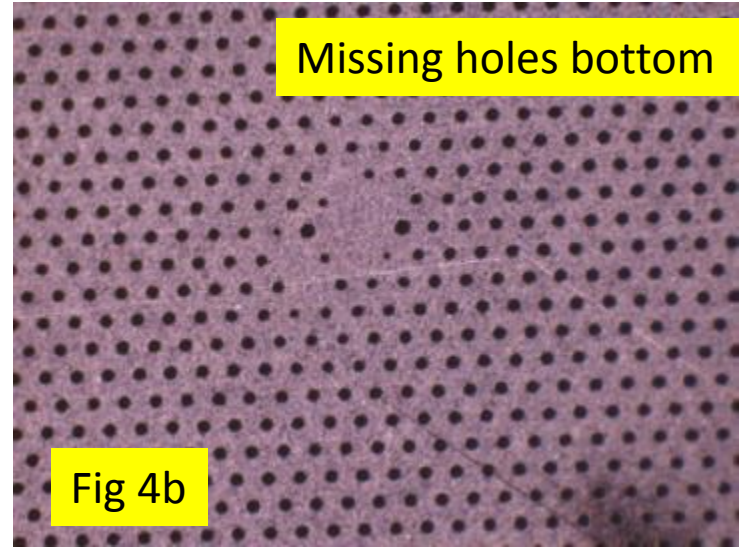
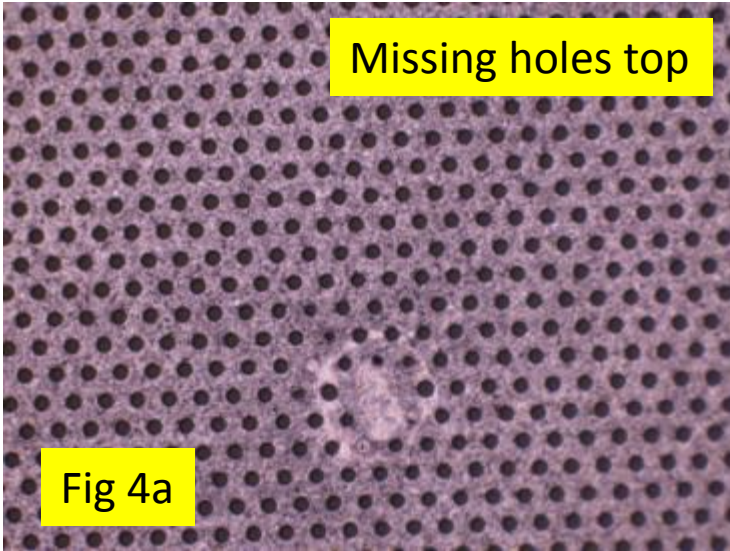
- **50 GEM foil total**
- **38 (76%) GEM foils OK**
  - **5 of them recovered after Rui's washing**
- **12 (24%) GEM foils BAD**
  - **8 problems in active area: 3 current leak, 1 short, 3 continuously discharging, 1 rough defined sector edge**
  - **4 external problems: 3 high resistance HV vias, 1 damaged HV tails**



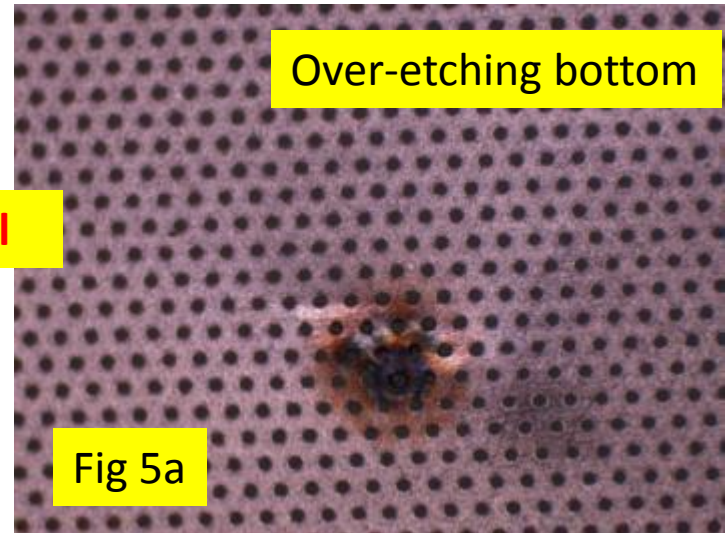
# GEM Zoology







Rejected foil



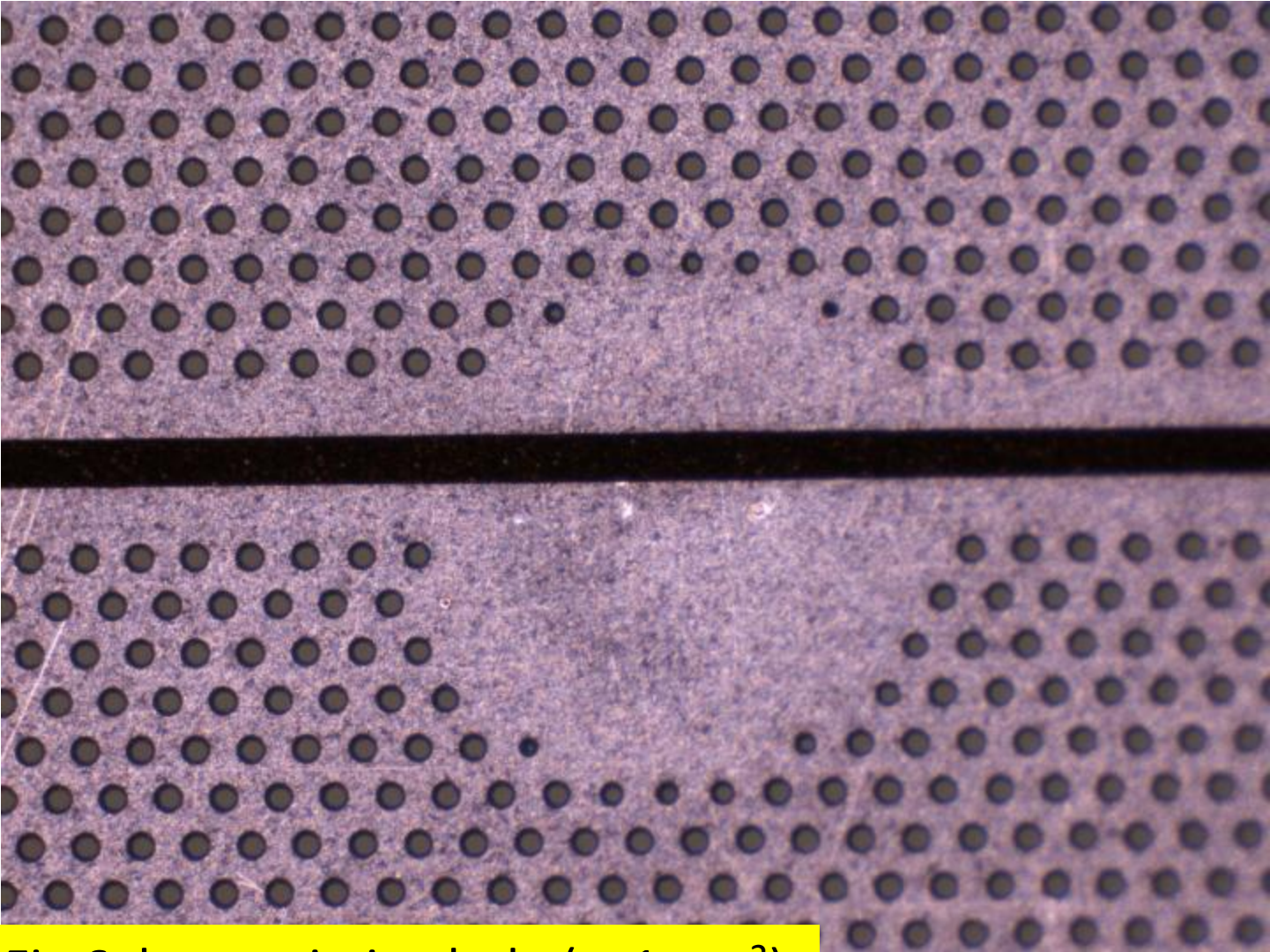


Fig 6: large missing hole (  $\sim 1\text{mm}^2$  )



Typical heavy “over-etching” with residual bottom copper film, leading to continuous discharges (all on the same foil!)

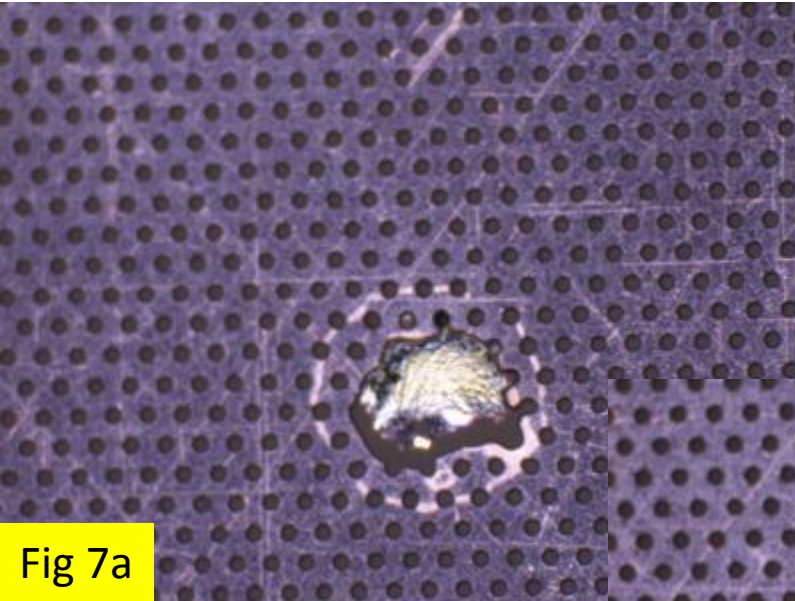


Fig 7a

**Rejected foil**

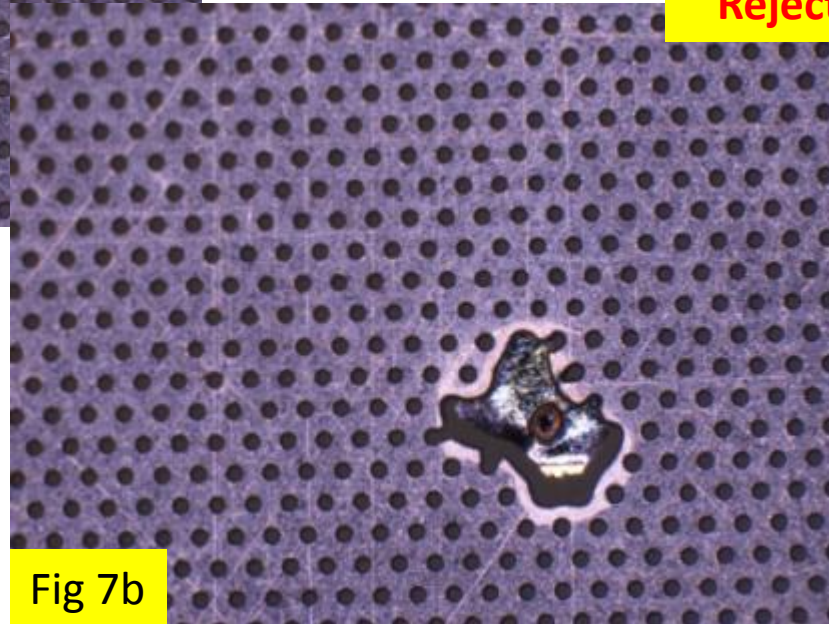


Fig 7b

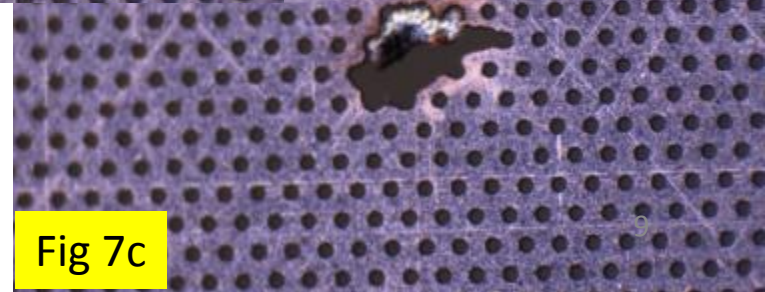
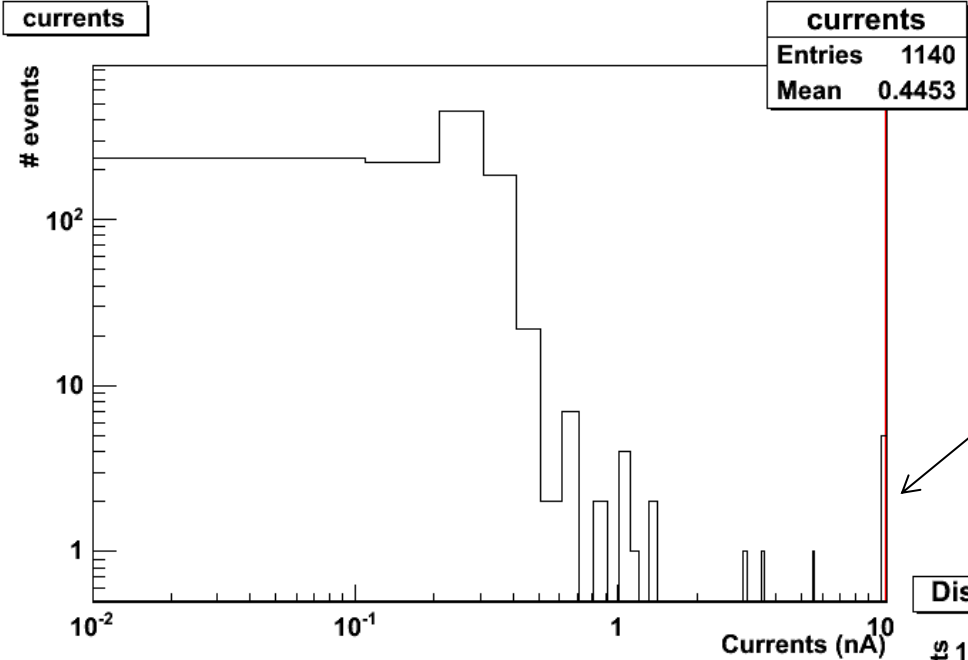


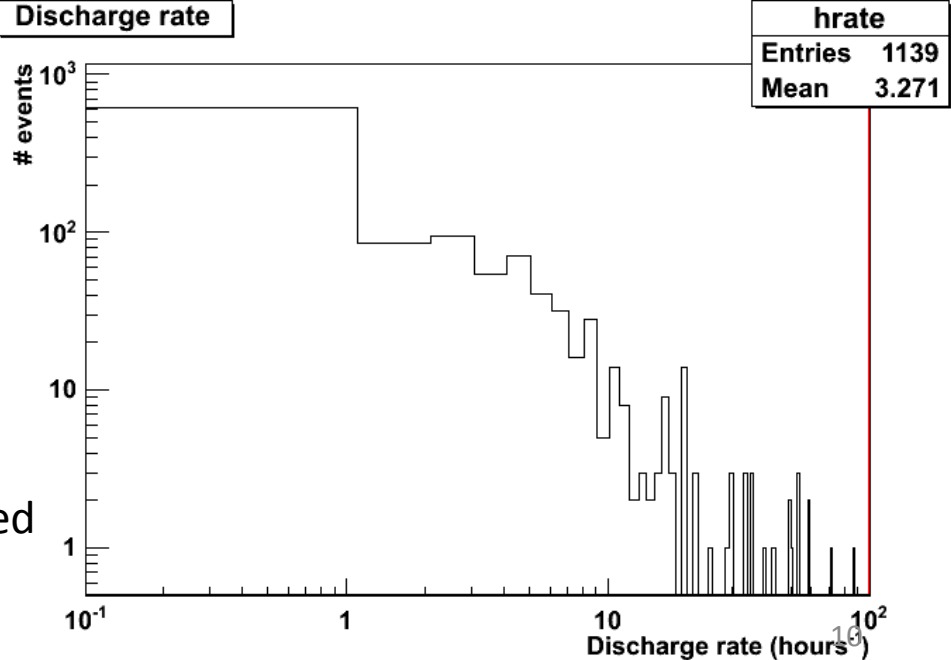
Fig 7c

# Current & Discharge rate per sector @ 600 V (in Nitrogen)



Layers 1,2,3

Discharges counted in 1 hour period



# Conclusions

- The GEM quality test is a high time consuming phase of a GEM detector construction
- The GEM production suffers various problems to be understood & kept under control: the most dangerous is probably the “over-etching” with a residual bottom copper film
- For KLOE the yield was 76% (84% if only active area problems are considered)